1SS413

SILICON EPITAXIAL S CHOTTKY BARRIER DIODE

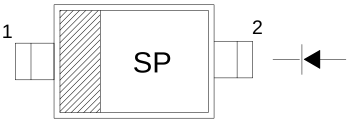
High Speed Switching Application

Features

- Low forward voltage : $V_{F(3)}$=0.50V(typ.).
- Low reverse current : I_R=0.5μA (max.).
- Small total capacitance : C_T=3.9pF (typ.).

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "SP"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings (T_j = 25?)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	25	V
Reverse Voltage	V_R	20	V
Peak Forward Current	I_{FM}	100	mA
Average Forward Current	I_O	50	mA
Surge Current (10ms)	I_{FSM}	1	A
Power Dissipation (Note 1)	P_{tot}	100	mW
Junction Temperature	T_J	125	?
Storage Temperature	T_s	-55 to +125	?

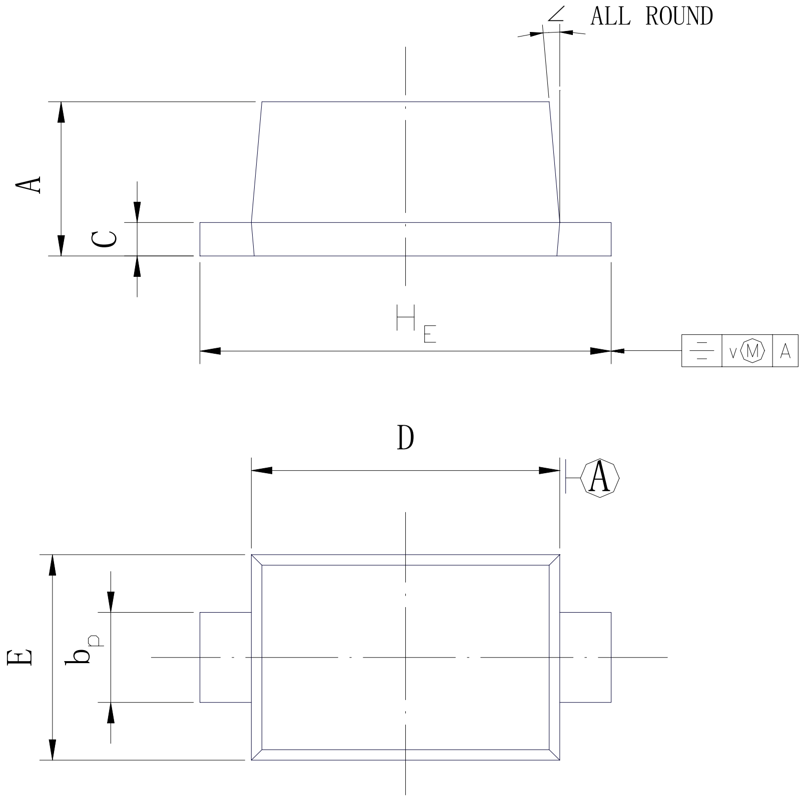
Note 1: Mounted on a glass epoxy circuit board of 20x20 mm, pad dimension of 4x4 mm.

Characteristics at T_j = 25 ?

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	I_F = 1mA	$V_{F(1)}$	-	0.33	-	V
	I_F = 5mA	$V_{F(2)}$	-	0.38	-	V
	I_F = 50mA	$V_{F(3)}$	-	0.50	0.55	V
Reverse Current	V_R = 20V	I_R	-	-	0.5	μA
Total Capacitance	V_R = 0V ,f = 1MH$_Z$	C_T	-	3.9	-	pF

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	v	∠
mm	0.70 0.60	0.4 0.3	0.135 0.127	1.25 1.15	0.85 0.75	1.65 1.55	0.1	5°